

**Abstract of the Disclosure**

A GaN layer is grown on a sapphire substrate, an SiO<sub>2</sub> film is formed on the GaN layer, and a GaN semiconductor layer including an MQW active layer is then grown on the GaN layer 5 and the SiO<sub>2</sub> film using epitaxial lateral overgrowth. The GaN based semiconductor layer is removed by etching except in a region on the SiO<sub>2</sub> film, and a p electrode is then formed on the top surface of the GaN based semiconductor layer on the SiO<sub>2</sub> film, to join the p electrode on the GaN based 10 semiconductor layer to an ohmic electrode on a GaAs substrate. An n electrode is formed on the top surface of the GaN based semiconductor layer.

100-200-300-400-500-600-700-800-900